

Phase Control Thyristor

Supersedes June 1997 version, DS4647 - 4.1

DS4647 - 4.2 March 1998

APPLICATIONS

- High Power Drives.
- High Voltage Power Supplies.
- DC Motor Control.

KEY PARAMETERS

$V_{_{\mathrm{DRM}}}$	3800V
I _{T(AV)}	1770A
I _{TSM}	36250A
dVdt*	500V /μ s
dl/dt	300A /μs

*Higher dV/dt selections available

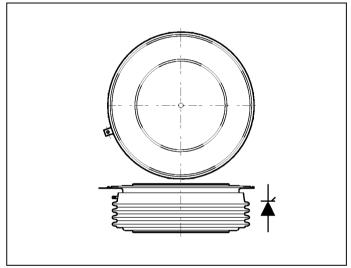
FEATURES

- Double Side Cooling.
- High Surge Capability.
- High Mean Current.
- Fatigue Free.

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
DCR1476SY38	3800	$T_{vi} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1476SY37	3700	$I_{DRM}^{v_j} = I_{RRM} = 250 \text{mA},$
DCR1476SY36	3600	V_{DRM} , V_{RRM} $t_p = 10 ms$,
DCR1476SY35	3500	V _{DSM} & V _{RSM} =
DCR1476SY34	3400	V _{DRM} & V _{RRM} + 100V
		Respectively

Lower voltage grades available.



Outline type code: Y. See package outline for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load, T _{case} = 80°C	1770	Α			
I _{T(RMS)}	RMS value	T _{case} = 80°C	2780	Α			
I _T	Continuous (direct) on-state current	T _{case} = 80°C	2530	Α			
Single Side	Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load, T _{case} = 80°C	1170	Α			
I _{T(RMS)}	RMS value	$T_{case} = 80^{\circ}C$	1837	А			
I _T	Continuous (direct) on-state current	$T_{case} = 80$ °C	1590	Α			

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	29.0	kA
l²t	I ² t for fusing	$V_R = 50\% V_{RRM} - 1/4 \text{ sine}$	4.21 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	36.25	kA
l ² t	I ² t for fusing	V _R = 0	6.57 x 10 ⁶	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
R _{th(j-c)} Thermal resistance - junction to case		Double side cooled	dc	-	0.0095	°C/W
	Thermal resistance - junction to case	Single side cooled	Anode dc	-	0.019	°C/W
			Cathode dc	-	0.019	°C/W
R _{th(c-h)} The		Clamping force 43.0kN with mounting compound	Double side	-	0.002	°C/W
			Single side	-	0.004	°C/W
T _{vj} Virtual junction temperature	Virtual junction temporature	On-state (conducting)		-	135	°C
	Virtual junction temperature	Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			38.0	47.0	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C			250	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V _{DRM} T _j = 125°C.		-	500	V/µs
117.11		I DRM I	Repetitive 50Hz	-	150	A/μs
dl/dt	Rate of rise of on-state current	Gate source 20V, 10Ω $t_r \le 0.5 \mu s$, $T_j = 125 ^{\circ} C$	Non-repetitive	-	300	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	1.03	٧
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.32	mΩ
t _{gd}	Delay time	$V_{_{D}}$ = 67% $V_{_{DRM}}$, Gate source 30V, 15 Ω $t_{_{r}}$ = 0.5 μ s, $T_{_{j}}$ = 25°C		-	2.5	μs
t _q	Turn-off time	$I_T = 1000A$, $t_p = 1$ ms, $T_j = 125$ °C, $V_R = 50V$, $dI_{RR}/dt = 2A/\mu$ s, $V_{DR} = 67\% V_{DRM}$, $dV_{DR}/dt = 8V/\mu$ s linear		600	800	μs
IL	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		300	1000	mA
I _H	Holding current	$T_j = 25$ °C, $R_{g-k} = \infty$		-	500	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Max.	Units
V _{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	4.0	٧
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	400	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	٧
V _{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	٧
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	٧
V _{RGM}	Peak reverse gate voltage		5	٧
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	Α
P _{GM}	Peak gate power	See table, fig.4	150	w
P _{G(AV)}	Mean gate power		10	W

CURVES

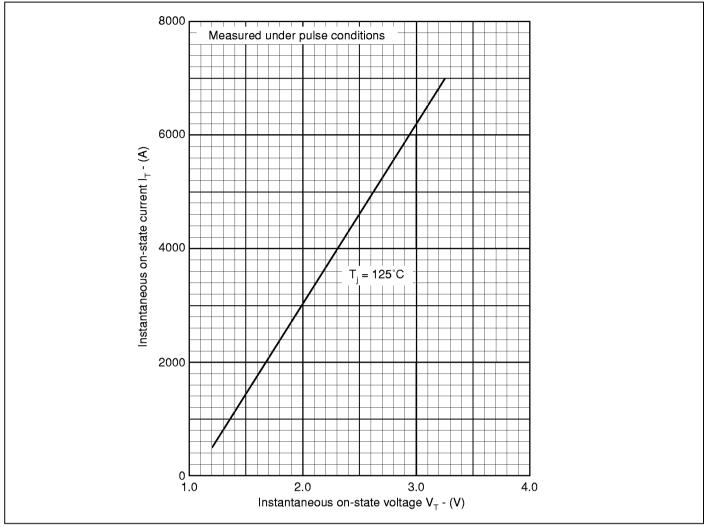


Fig.1 Maximum (limit) on-state characteristics

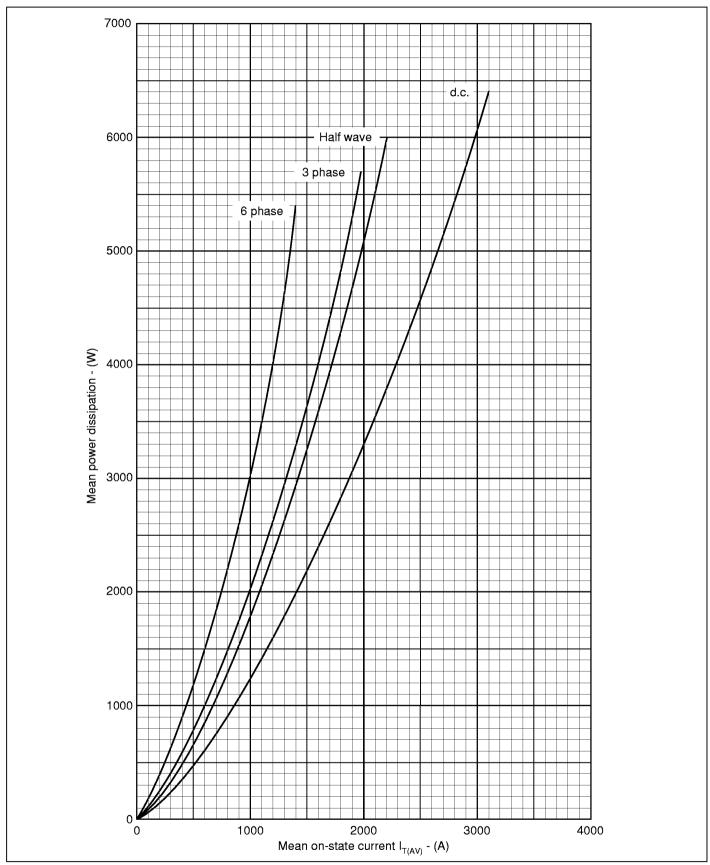


Fig.2 Dissipation curves

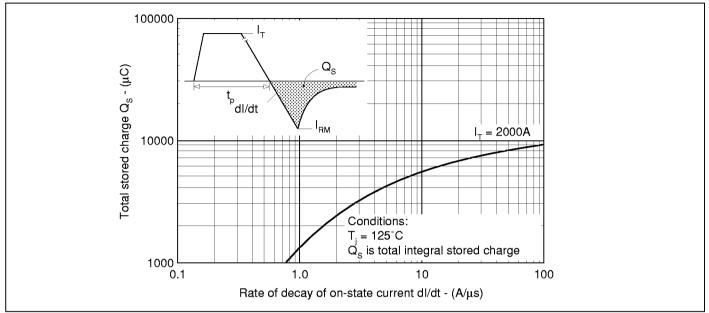


Fig.3 Stored charge

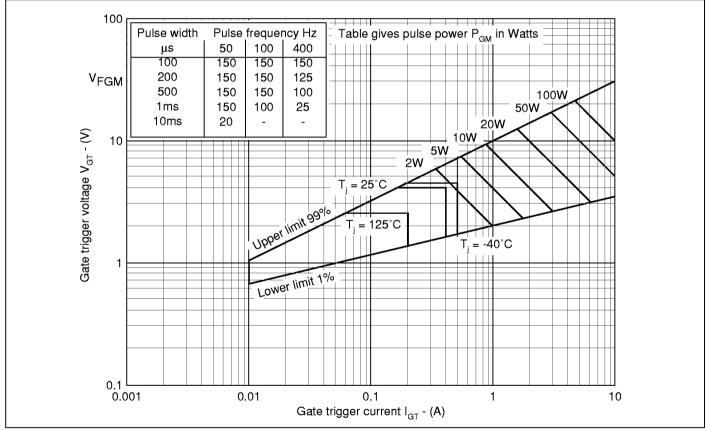


Fig.4 Gate characteristics

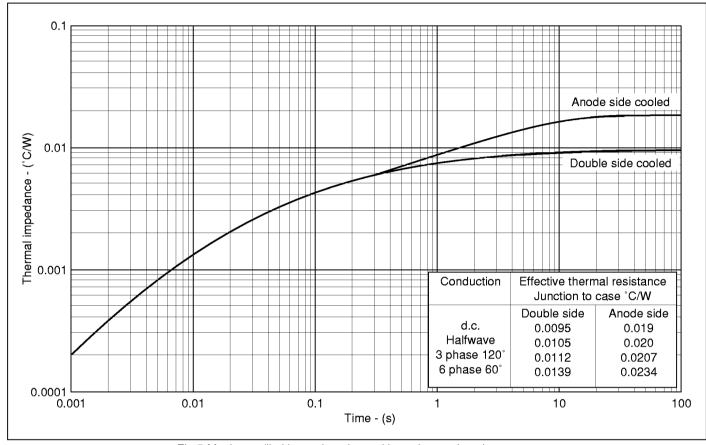


Fig.5 Maximum (limit) transient thermal impedance - junction to case

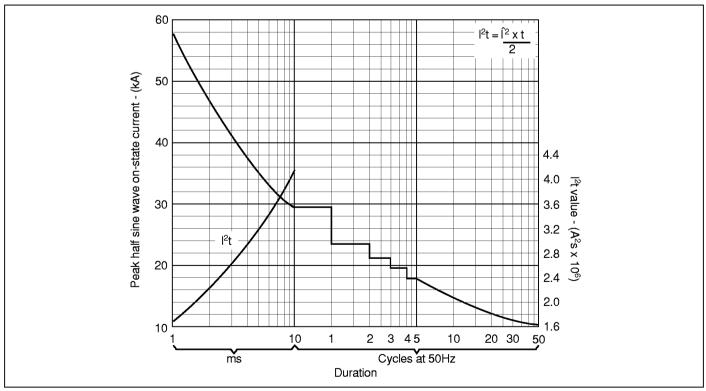
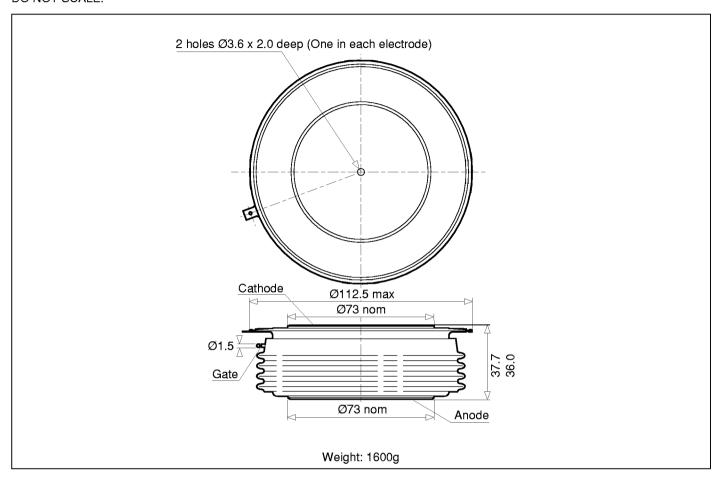


Fig.6 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} at T_{case} 125°C)

PACKAGE OUTLINE - Y

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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